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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	I ² C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	12
Program Memory Size	12KB (4K x 24)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	28-VQFN Exposed Pad
Supplier Device Package	28-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f2011t-20e-ml

dsPIC30F Flash Programming Specification

3.0 PROGRAMMING EXECUTIVE APPLICATION

3.1 Programming Executive Overview

The programming executive resides in executive memory and is executed when Enhanced ICSP Programming mode is entered. The programming executive provides the mechanism for the programmer (host device) to program and verify the dsPIC30F, using a simple command set and communication protocol.

The following capabilities are provided by the programming executive:

- Read memory
 - Code memory and data EEPROM
 - Configuration registers
 - Device ID
- Erase memory
 - Bulk Erase by segment
 - Code memory (by row)
 - Data EEPROM (by row)
- Program memory
 - Code memory
 - Data EEPROM
 - Configuration registers
- Query
 - Blank Device
 - Programming executive software version

The programming executive performs the low-level tasks required for erasing and programming. This allows the programmer to program the device by issuing the appropriate commands and data.

The programming procedure is outlined in [Section 5.0 “Device Programming”](#).

3.2 Programming Executive Code Memory

The programming executive is stored in executive code memory and executes from this reserved region of memory. It requires no resources from user code memory or data EEPROM.

3.3 Programming Executive Data RAM

The programming executive uses the device's data RAM for variable storage and program execution. Once the programming executive has run, no assumptions should be made about the contents of data RAM.

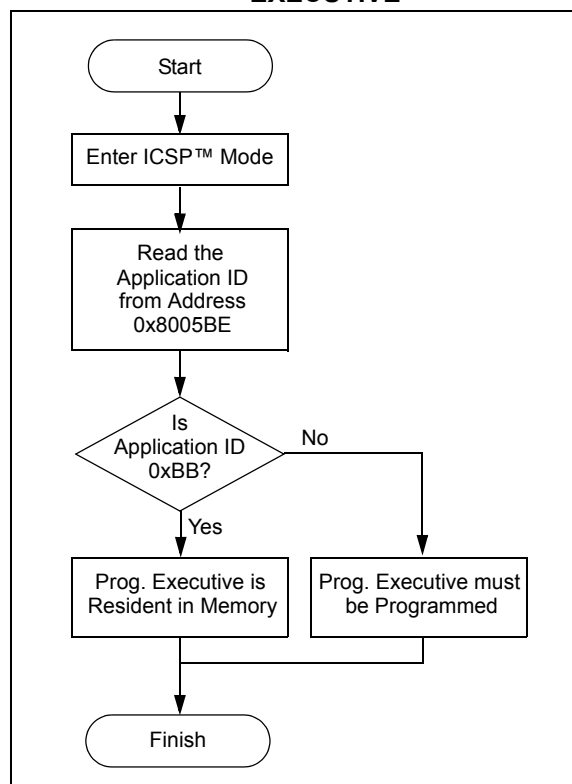
4.0 CONFIRMING THE CONTENTS OF EXECUTIVE MEMORY

Before programming can begin, the programmer must confirm that the programming executive is stored in executive memory. The procedure for this task is illustrated in [Figure 4-1](#).

First, ICSP mode is entered. The unique application ID word stored in executive memory is then read. If the programming executive is resident, the application ID word is 0xBB, which means programming can resume as normal. However, if the application ID word is not 0xBB, the programming executive must be programmed to Executive Code memory using the method described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

[Section 11.0 “ICSP™ Mode”](#) describes the process for the ICSP programming method. [Section 11.13 “Reading the Application ID Word”](#) describes the procedure for reading the application ID word in ICSP mode.

FIGURE 4-1: CONFIRMING PRESENCE OF THE PROGRAMMING EXECUTIVE



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5.5 Code Memory Programming

5.5.1 OVERVIEW

The Flash code memory array consists of 512 rows of thirty-two, 24-bit instructions. Each panel stores 16K instruction words, and each dsPIC30F device has either 1, 2 or 3 memory panels (see [Table 5-2](#)).

TABLE 5-2: DEVICE CODE MEMORY SIZE

Device	Code Size (24-bit Words)	Number of Rows	Number of Panels
dsPIC30F2010	4K	128	1
dsPIC30F2011	4K	128	1
dsPIC30F2012	4K	128	1
dsPIC30F3010	8K	256	1
dsPIC30F3011	8K	256	1
dsPIC30F3012	8K	256	1
dsPIC30F3013	8K	256	1
dsPIC30F3014	8K	256	1
dsPIC30F4011	16K	512	1
dsPIC30F4012	16K	512	1
dsPIC30F4013	16K	512	1
dsPIC30F5011	22K	704	2
dsPIC30F5013	22K	704	2
dsPIC30F5015	22K	704	2
dsPIC30F5016	22K	704	2
dsPIC30F6010	48K	1536	3
dsPIC30F6010A	48K	1536	3
dsPIC30F6011	44K	1408	3
dsPIC30F6011A	44K	1408	3
dsPIC30F6012	48K	1536	3
dsPIC30F6012A	48K	1536	3
dsPIC30F6013	44K	1408	3
dsPIC30F6013A	44K	1408	3
dsPIC30F6014	48K	1536	3
dsPIC30F6014A	48K	1536	3
dsPIC30F6015	48K	1536	3

5.5.2 PROGRAMMING METHODOLOGY

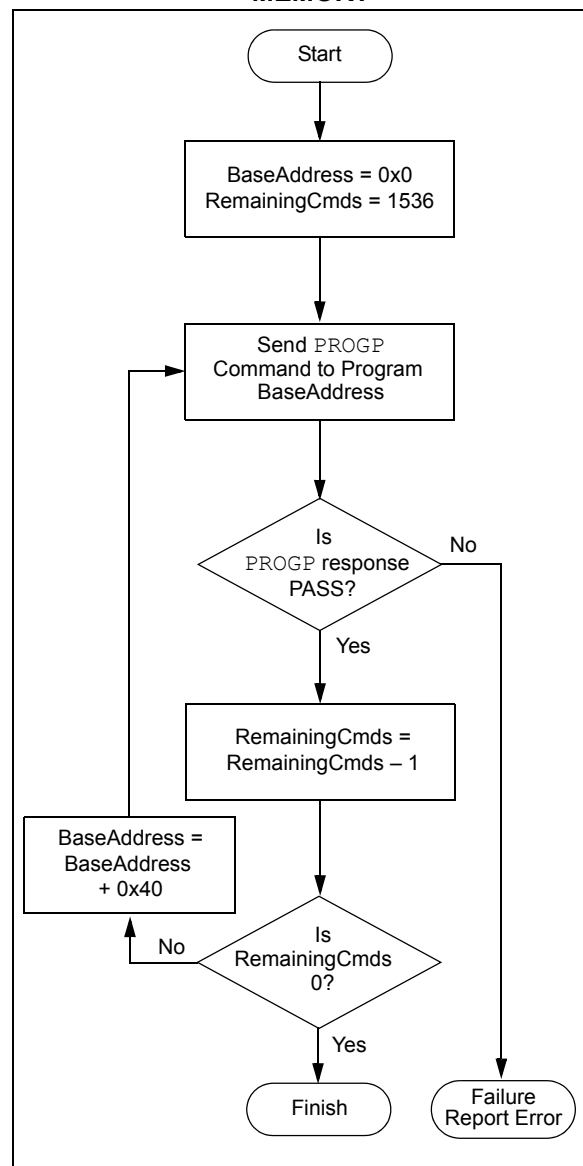
Code memory is programmed with the `PROGP` command. `PROGP` programs one row of code memory to the memory address specified in the command. The number of `PROGP` commands required to program a device depends on the number of rows that must be programmed in the device.

A flowchart for programming of code memory is illustrated in [Figure 5-3](#). In this example, all 48K instruction words of a dsPIC30F6014A device are programmed. First, the number of commands to send (called 'RemainingCmds' in the flowchart) is set to 1536 and the destination address (called 'BaseAddress') is set to '0'.

Next, one row in the device is programmed with a `PROGP` command. Each `PROGP` command contains data for one row of code memory of the dsPIC30F6014A. After the first command is processed successfully, 'RemainingCmds' is decremented by 1 and compared to 0. Since there are more `PROGP` commands to send, 'BaseAddress' is incremented by 0x40 to point to the next row of memory.

On the second `PROGP` command, the second row of each memory panel is programmed. This process is repeated until the entire device is programmed. No special handling must be performed when a panel boundary is crossed.

FIGURE 5-3: FLOWCHART FOR PROGRAMMING dsPIC30F6014A CODE MEMORY



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TABLE 5-7: CONFIGURATION BITS DESCRIPTION

Bit Field	Register	Description
FWPSA<1:0>	FWDT	Watchdog Timer Prescaler A 11 = 1:512 10 = 1:64 01 = 1:8 00 = 1:1
FWPSB<3:0>	FWDT	Watchdog Timer Prescaler B 1111 = 1:16 1110 = 1:15 . . . 0001 = 1:2 0000 = 1:1
FWDTEN	FWDT	Watchdog Enable 1 = Watchdog enabled (LPRC oscillator cannot be disabled. Clearing the SWDTEN bit in the RCON register will have no effect) 0 = Watchdog disabled (LPRC oscillator can be disabled by clearing the SWDTEN bit in the RCON register)
MCLREN	FBORPOR	Master Clear Enable 1 = Master Clear pin (MCLR) is enabled 0 = MCLR pin is disabled
PWMPIN	FBORPOR	Motor Control PWM Module Pin Mode 1 = PWM module pins controlled by PORT register at device Reset (tri-stated) 0 = PWM module pins controlled by PWM module at device Reset (configured as output pins)
HPOL	FBORPOR	Motor Control PWM Module High-Side Polarity 1 = PWM module high-side output pins have active-high output polarity 0 = PWM module high-side output pins have active-low output polarity
LPOL	FBORPOR	Motor Control PWM Module Low-Side Polarity 1 = PWM module low-side output pins have active-high output polarity 0 = PWM module low-side output pins have active-low output polarity
BOREN	FBORPOR	PBOR Enable 1 = PBOR enabled 0 = PBOR disabled
BORV<1:0>	FBORPOR	Brown-out Voltage Select 11 = 2.0V (not a valid operating selection) 10 = 2.7V 01 = 4.2V 00 = 4.5V
FPWRT<1:0>	FBORPOR	Power-on Reset Timer Value Select 11 = PWRT = 64 ms 10 = PWRT = 16 ms 01 = PWRT = 4 ms 00 = Power-up Timer disabled
RBS<1:0>	FBS	Boot Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = No Data RAM is reserved for Boot Segment 10 = Small-sized Boot RAM [128 bytes of RAM are reserved for Boot Segment] 01 = Medium-sized Boot RAM [256 bytes of RAM are reserved for Boot Segment] 00 = Large-sized Boot RAM [512 bytes of RAM are reserved for Boot Segment in dsPIC30F5011/5013, and 1024 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015]

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TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

Bit Field	Register	Description
SSS<2:0>	FSS	Secure Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 111 = No Secure Segment 110 = Standard security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 101 = Standard security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 100 = Standard security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = No Secure Segment 010 = High security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 000 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF]
SWRP	FSS	Secure Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = Secure Segment program memory is not write-protected 0 = Secure program memory is write-protected
GSS<1:0>	FGS	General Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = Code protection is disabled 10 = Standard security code protection is enabled 0x = High security code protection is enabled
GCP	FGS	General Segment Program Memory Code Protection (present in all devices except dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = General Segment program memory is not code-protected 0 = General Segment program memory is code-protected
GWRP	FGS	General Segment Program Memory Write Protection 1 = General Segment program memory is not write-protected 0 = General Segment program memory is write-protected
BKBUG	FICD	Debugger/Emulator Enable 1 = Device will reset into Operational mode 0 = Device will reset into Debug/Emulation mode
COE	FICD	Debugger/Emulator Enable 1 = Device will reset into Operational mode 0 = Device will reset into Clip-on Emulation mode
ICS<1:0>	FICD	ICD Communication Channel Select 11 = Communicate on PGC/EMUC and PGD/EMUD 10 = Communicate on EMUC1 and EMUD1 01 = Communicate on EMUC2 and EMUD2 00 = Communicate on EMUC3 and EMUD3
RESERVED	FBS, FSS, FGS	Reserved (read as '1', write as '1')
—	All	Unimplemented (read as '0', write as '0')

TABLE 5-10: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013 AND dsPIC30F5015/5016)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	FOS<2:0>			—	—	—	FPR<4:0>				
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN ⁽¹⁾	HPOL ⁽¹⁾	LPOL ⁽¹⁾	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	Reserved ⁽²⁾		—	—	—	Reserved ⁽²⁾	—	—	—	—	Reserved ⁽²⁾			
0xF80008	FSS	—	—	Reserved ⁽²⁾		—	—	Reserved ⁽²⁾		—	—	—	—	Reserved ⁽²⁾			
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	Reserved ⁽³⁾	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

Note 1: On the 2011, 2012, 3012, 3013, 3014 and 4013, these bits are reserved (read as '1' and must be programmed as '1').
2: Reserved bits read as '1' and must be programmed as '1'.
3: The FGS<2> bit is a read-only copy of the GCP bit (FGS<1>).

TABLE 5-11: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015)

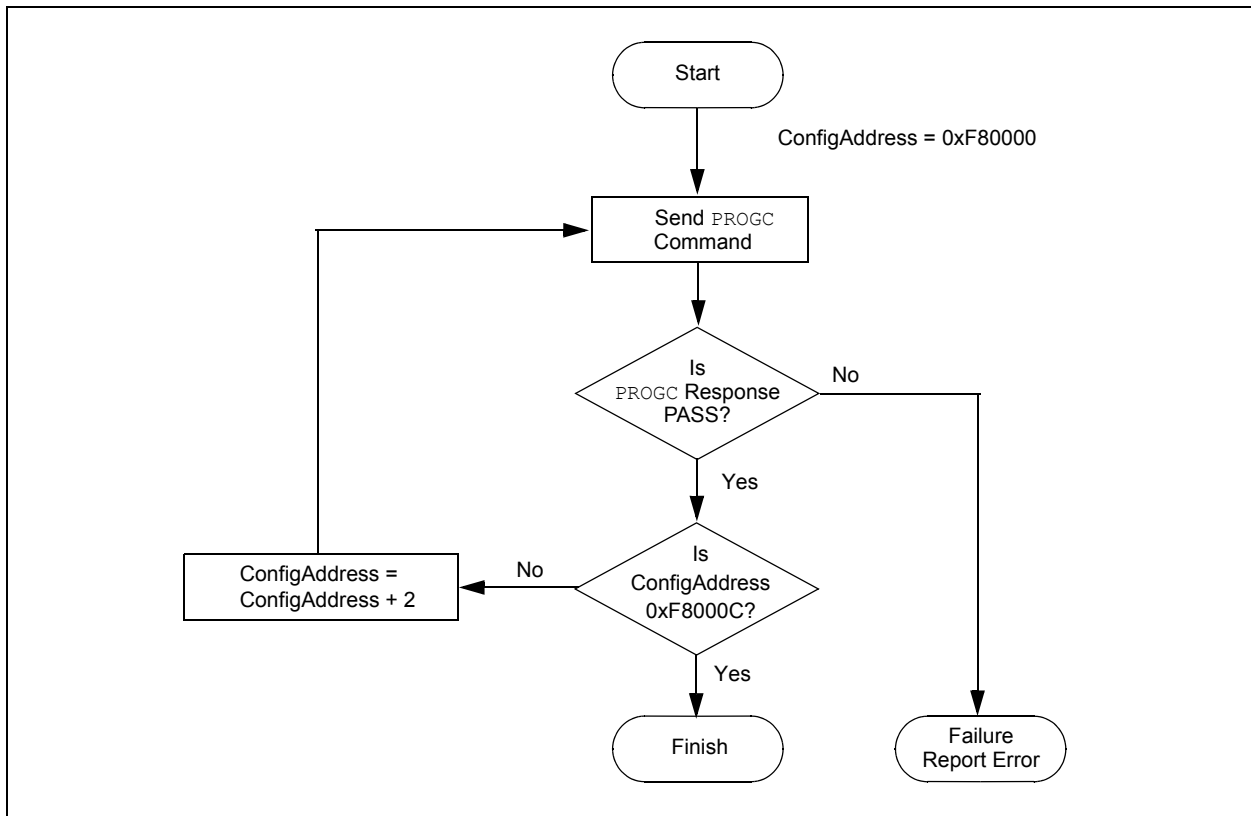
Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	FOS<2:0>			—	—	—	FPR<4:0>				
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN ⁽¹⁾	HPOL ⁽¹⁾	LPOL ⁽¹⁾	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	RBS<1:0>		—	—	—	EBS	—	—	—	—	BSS<2:0>			BWRP
0xF80008	FSS	—	—	RSS<1:0>		—	—	ESS<1:0>		—	—	—	—	SSS<2:0>			SWRP
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	GSS<1:0>		GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

Note 1: On the 6011A, 6012A, 6013A and 6014A, these bits are reserved (read as '1' and must be programmed as '1').

5.8 Exiting Enhanced ICSP Mode

The Enhanced ICSP mode is exited by removing power from the device or bringing MCLR to VIL. When normal user mode is next entered, the program that was stored using Enhanced ICSP will execute.

FIGURE 5-5: CONFIGURATION BIT PROGRAMMING FLOW



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6.0 OTHER PROGRAMMING FEATURES

6.1 Erasing Memory

Memory is erased by using an `ERASEB`, `ERASED` or `ERASEP` command, as detailed in [Section 8.5 “Command Descriptions”](#). Code memory can be erased by row using `ERASEP`. Data EEPROM can be erased by row using `ERASED`. When memory is erased, the affected memory locations are set to ‘1’s.

`ERASEB` provides several Bulk Erase options. Performing a Chip Erase with the `ERASEB` command clears all code memory, data EEPROM and code protection registers. Alternatively, `ERASEB` can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in [Table 6-1](#).

TABLE 6-1: ERASE OPTIONS

Command	Affected Region
<code>ERASEB</code>	Entire chip ⁽¹⁾ or all code memory or all data EEPROM, or erase by segment
<code>ERASED</code>	Specified rows of data EEPROM
<code>ERASEP</code> ⁽²⁾	Specified rows of code memory

- Note 1:** The system operation Configuration registers and device ID registers are not erasable.
- 2:** `ERASEP` cannot be used to erase code-protect Configuration bits. These bits must be erased using `ERASEB`.

6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using `ERASEP` and `ERASED`, respectively. You can then reprogram the modified rows with the `PROGP` and `PROGD` command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the `PROGP` command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the `ERASEB` command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select)

field in the `ERASEB` command. The code-protect Configuration bits can then be reprogrammed using the `PROGC` command.

Note: If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

6.3 Reading Memory

The `READD` command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. `READD` can be used to return the entire contents of data EEPROM.

The `READP` command reads the code memory of the device. This command only returns 24-bit data packed as described in [Section 8.3 “Packed Data Format”](#). `READP` can be used to read up to 32K instruction words of code memory.

Note: Reading an unimplemented memory location causes the programming executive to reset. All `READD` and `READP` commands **must** specify only valid memory locations.

6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The `QVER` command performs this function. See [Section 8.5.11 “QVER Command”](#) for more details about this command.

6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

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6.6 Configuration Information in the Hexadecimal File

To allow portability of code, the programmer must read the Configuration register locations from the hexadecimal file. If configuration information is not present in the hexadecimal file, a simple warning message should be issued by the programmer. Similarly, while saving a hexadecimal file, all configuration information must be included. An option to not include the configuration information can be provided.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

6.7 Unit ID

The dsPIC30F devices contain 32 instructions of Unit ID. These are located at addresses 0x8005C0 through 0x8005FF. The Unit ID can be used for storing product information such as serial numbers, system manufacturing dates, manufacturing lot numbers and other such application-specific information.

A Bulk Erase does not erase the Unit ID locations. Instead, erase all executive memory using steps 1-4 as shown in [Table 12-1](#), and program the Unit ID along with the programming executive. Alternately, use a Row Erase to erase the row containing the Unit ID locations.

6.8 Checksum Computation

Checksums for the dsPIC30F are 16 bits in size. The checksum is to total sum of the following:

- Contents of code memory locations
- Contents of Configuration registers

[Table A-1](#) describes how to calculate the checksum for each device. All memory locations are summed one byte at a time, using only their native data size. More specifically, Configuration and device ID registers are summed by adding the lower two bytes of these locations (the upper byte is ignored), while code memory is summed by adding all three bytes of code memory.

Note: The checksum calculation differs depending on the code-protect setting. [Table A-1](#) describes how to compute the checksum for an unprotected device and a read-protected device. Regardless of the code-protect setting, the Configuration registers can always be read.

7.0 PROGRAMMER – PROGRAMMING EXECUTIVE COMMUNICATION

7.1 Communication Overview

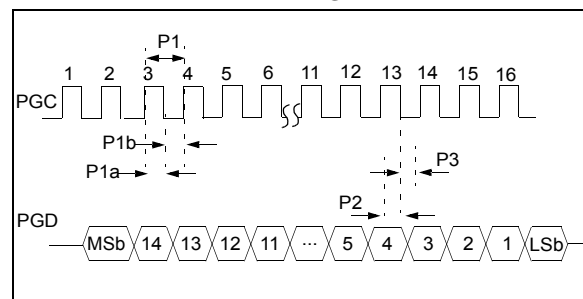
The programmer and programming executive have a master-slave relationship, where the programmer is the master programming device and the programming executive is the slave.

All communication is initiated by the programmer in the form of a command. Only one command at a time can be sent to the programming executive. In turn, the programming executive only sends one response to the programmer after receiving and processing a command. The programming executive command set is described in [Section 8.0 “Programming Executive Commands”](#). The response set is described in [Section 9.0 “Programming Executive Responses”](#).

7.2 Communication Interface and Protocol

The Enhanced ICSP interface is a 2-wire SPI interface implemented using the PGC and PGD pins. The PGC pin is used as a clock input pin, and the clock source must be provided by the programmer. The PGD pin is used for sending command data to, and receiving response data from, the programming executive. All serial data is transmitted on the falling edge of PGC and latched on the rising edge of PGD. All data transmissions are sent Most Significant bit (MSb) first, using 16-bit mode (see [Figure 7-1](#)).

FIGURE 7-1: PROGRAMMING EXECUTIVE SERIAL TIMING



Since a 2-wire SPI interface is used, and data transmissions are bidirectional, a simple protocol is used to control the direction of PGD. When the programmer completes a command transmission, it releases the PGD line and allows the programming executive to drive this line high. The programming executive keeps the PGD line high to indicate that it is processing the command.

After the programming executive has processed the command, it brings PGD low for 15 μ sec to indicate to the programmer that the response is available to be

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clocked out. The programmer can begin to clock out the response 20 μ sec after PGD is brought low, and it must provide the necessary amount of clock pulses to receive the entire response from the programming executive.

Once the entire response is clocked out, the programmer should terminate the clock on PGC until it is time to send another command to the programming executive. This protocol is illustrated in Figure 7-2.

7.3 SPI Rate

In Enhanced ICSP mode, the dsPIC30F operates from the fast internal RC oscillator, which has a nominal frequency of 7.37 MHz. This oscillator frequency yields an effective system clock frequency of 1.84 MHz. Since the SPI module operates in Slave mode, the programmer must limit the SPI clock rate to a frequency no greater than 1 MHz.

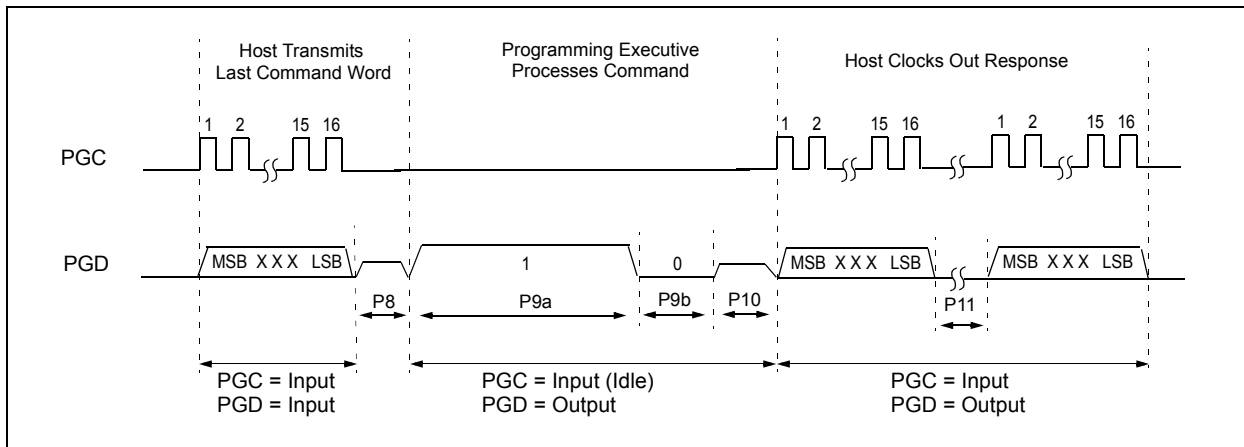
Note: If the programmer provides the SPI with a clock faster than 1 MHz, the behavior of the programming executive will be unpredictable.

7.4 Time Outs

The programming executive uses no Watchdog Timer or time out for transmitting responses to the programmer. If the programmer does not follow the flow control mechanism using PGC, as described in [Section 7.2 “Communication Interface and Protocol”](#), it is possible that the programming executive will behave unexpectedly while trying to send a response to the programmer. Since the programming executive has no time out, it is imperative that the programmer correctly follow the described communication protocol.

As a safety measure, the programmer should use the command time outs identified in [Table 8-1](#). If the command time out expires, the programmer should reset the programming executive and start programming the device again.

FIGURE 7-2: PROGRAMMING EXECUTIVE – PROGRAMMER COMMUNICATION PROTOCOL



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TABLE 8-1: PROGRAMMING EXECUTIVE COMMAND SET

Opcode	Mnemonic	Length (16-bit words)	Time Out	Description
0x0	SCHECK	1	1 ms	Sanity check.
0x1	READD	4	1 ms/row	Read N 16-bit words of data EEPROM, Configuration registers or device ID starting from specified address.
0x2	READP	4	1 ms/row	Read N 24-bit instruction words of code memory starting from specified address.
0x3	Reserved	N/A	N/A	This command is reserved. It will return a NACK.
0x4	PROGD ⁽²⁾	19	5 ms	Program one row of data EEPROM at the specified address, then verify.
0x5	PROGP ⁽¹⁾	51	5 ms	Program one row of code memory at the specified address, then verify.
0x6	PROGC	4	5 ms	Write byte or 16-bit word to specified Configuration register.
0x7	ERASEB	2	5 ms	Bulk Erase (entire code memory or data EEPROM), or erase by segment.
0x8	ERASED ⁽²⁾	3	5 ms/row	Erase rows of data EEPROM from specified address.
0x9	ERASEP ⁽¹⁾	3	5 ms/row	Erase rows of code memory from specified address.
0xA	QBLANK	3	300 ms	Query if the code memory and data EEPROM are blank.
0xB	QVER	1	1 ms	Query the programming executive software version.

Note 1: One row of code memory consists of (32) 24-bit words. Refer to [Table 5-2](#) for device-specific information.

Note 2: One row of data EEPROM consists of (16) 16-bit words. Refer to [Table 5-3](#) for device-specific information.

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8.5.5 PROGp COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_N					

Field	Description
Opcode	0x5
Length	0x33
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data word 3 through 47
D_48	16-bit data word 48

The **PROGP** command instructs the programming executive to program one row of code memory (32 instruction words) to the specified memory address. Programming begins with the row address specified in the command. The destination address should be a multiple of 0x40.

The data to program to memory, located in command words D_1 through D_48, must be arranged using the packed instruction word format shown in [Figure 8-2](#).

After all data has been programmed to code memory, the programming executive verifies the programmed data against the data in the command.

Expected Response (2 words):

0x1500
0x0002

Note: Refer to [Table 5-2](#) for code memory size information.

8.5.6 PROGc COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
Data					

Field	Description
Opcode	0x6
Length	0x4
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
Data	Data to program

The **PROGC** command programs data to the specified Configuration register and verifies the programming. Configuration registers are 16 bits wide, and this command allows one Configuration register to be programmed.

Expected Response (2 words):

0x1600
0x0002

Note: This command can only be used for programming Configuration registers.

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8.5.11 QVER COMMAND

15	12	11	0
Opcode	Length		

Field	Description
Opcode	0xB
Length	0x1

The QVER command queries the version of the programming executive software stored in test memory. The “version.revision” information is returned in the response’s QE_Code using a single byte with the following format: main version in upper nibble and revision in the lower nibble (i.e., 0x23 is version 2.3 of programming executive software).

Expected Response (2 words):

0x1BMN (where “MN” stands for version M.N)
0x0002

9.0 PROGRAMMING EXECUTIVE RESPONSES

9.1 Overview

The programming executive sends a response to the programmer for each command that it receives. The response indicates if the command was processed correctly, and includes any required response or error data.

The programming executive response set is shown in Table 9-1. This table contains the opcode, mnemonic and description for each response. The response format is described in Section 9.2 “Response Format”.

TABLE 9-1: PROGRAMMING EXECUTIVE RESPONSE SET

Opcode	Mnemonic	Description
0x1	PASS	Command successfully processed.
0x2	FAIL	Command unsuccessfully processed.
0x3	NACK	Command not known.

9.2 Response Format

As shown in Example 9-1, all programming executive responses have a general format consisting of a two word header and any required data for the command. Table 9-2 lists the fields and their descriptions.

EXAMPLE 9-1: FORMAT

15	12	11	8	7	0
Opcode	Last_Cmd		QE_Code		
Length					
D_1 (if applicable)					
...					
D_N (if applicable)					

TABLE 9-2: FIELDS AND DESCRIPTIONS

Field	Description
Opcode	Response opcode.
Last_Cmd	Programmer command that generated the response.
QE_Code	Query code or Error code.
Length	Response length in 16-bit words (includes 2 header words.)
D_1	First 16-bit data word (if applicable).
D_N	Last 16-bit data word (if applicable).

9.2.1 Opcode FIELD

The Opcode is a 4-bit field in the first word of the response. The Opcode indicates how the command was processed (see Table 9-1). If the command is processed successfully, the response opcode is PASS. If there is an error in processing the command, the response opcode is FAIL, and the QE_Code indicates the reason for the failure. If the command sent to the programming executive is not identified, the programming executive returns a NACK response.

9.2.2 Last_Cmd FIELD

The Last_Cmd is a 4-bit field in the first word of the response and indicates the command that the programming executive processed. Since the programming executive can only process one command at a time, this field is technically not required. However, it can be used to verify whether the programming executive correctly received the command that the programmer transmitted.

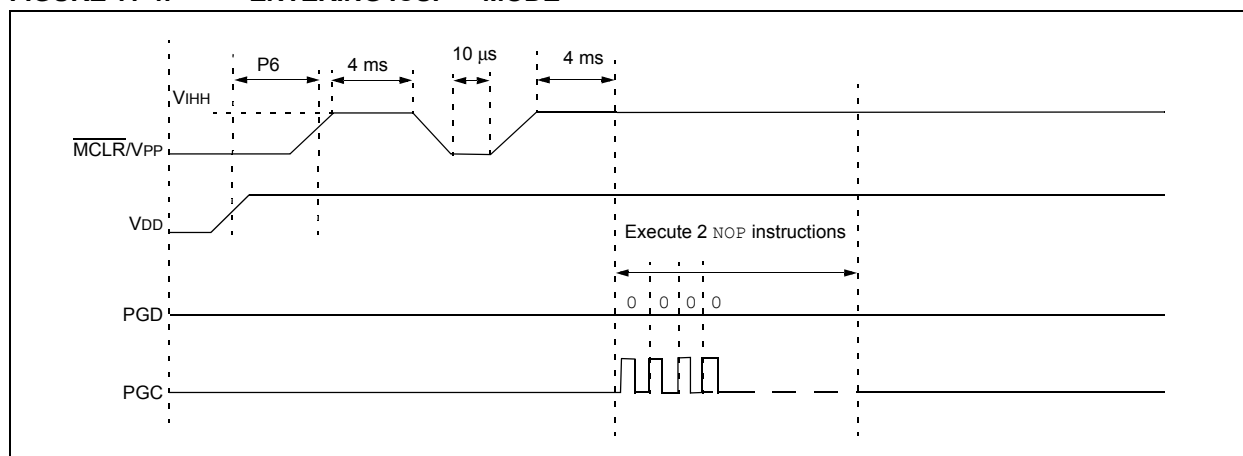
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11.3 Entering ICSP Mode

The ICSP mode is entered by holding PGC and PGD low, raising MCLR/VPP to VIH (high voltage), and then performing additional steps as illustrated in Figure 11-4.

- Note 1:** The sequence that places the device into ICSP mode places all unused I/O pins to the high-impedance state.
- 2:** Once ICSP mode is entered, the PC is set to 0x0 (the Reset vector).
- 3:** Before leaving the Reset vector, execute two GOTO instructions, followed by a single NOP instruction must be executed.

FIGURE 11-4: ENTERING ICSP™ MODE



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11.4 Flash Memory Programming in ICSP Mode

Programming in ICSP mode is described in [Section 11.4.1 “Programming Operations”](#) through [Section 11.4.3 “Starting and Stopping a Programming Cycle”](#). Step-by-step procedures are described in [Section 11.5 “Erasing Program Memory in Normal-Voltage Systems”](#) through [Section 11.13 “Reading the Application ID Word”](#). All programming operations must use serial execution, as described in [Section 11.2 “ICSP Operation”](#).

11.4.1 PROGRAMMING OPERATIONS

Flash memory write and erase operations are controlled by the NVMCON register. Programming is performed by setting NVMCON to select the type of erase operation ([Table 11-2](#)) or write operation ([Table 11-3](#)), writing a key sequence to enable the programming and initiating the programming by setting the WR control bit, NVMCON<15>.

In ICSP mode, all programming operations are externally timed. An external 2 ms delay must be used between setting the WR control bit and clearing the WR control bit to complete the programming operation.

TABLE 11-2: NVMCON ERASE OPERATIONS

NVMCON Value	Erase Operation
0x407F	Erase all code memory, data memory (does not erase UNIT ID).
0x4075	Erase 1 row (16 words) of data EEPROM.
0x4074	Erase 1 word of data EEPROM.
0x4072	Erase all executive memory.
0x4071	Erase 1 row (32 instruction words) from 1 panel of code memory.
0x406E	Erase Boot Secure and General Segments, then erase FBS, FSS and FGS configuration registers.
0x4066	Erase all Data EEPROM allocated to Boot Segment.
0x405E	Erase Secure and General Segments, then erase FSS and FGS configuration registers.
0x4056	Erase all Data EEPROM allocated to Secure Segment.
0x404E	Erase General Segment, then erase FGS configuration register.
0x4046	Erase all Data EEPROM allocated to General Segment.

TABLE 11-3: NVMCON WRITE OPERATIONS

NVMCON Value	Write Operation
0x4008	Write 1 word to configuration memory.
0x4005	Write 1 row (16 words) to data memory.
0x4004	Write 1 word to data memory.
0x4001	Write 1 row (32 instruction words) into 1 panel of program memory.

11.4.2 UNLOCKING NVMCON FOR PROGRAMMING

Writes to the WR bit (NVMCON<15>) are locked to prevent accidental programming from taking place. Writing a key sequence to the NVMKEY register unlocks the WR bit and allows it to be written to. The unlock sequence is performed as follows:

```
MOV    #0x55, W8
MOV    W8, NVMKEY
MOV    #0xAA, W9
MOV    W9, NVMKEY
```

Note: Any working register, or working register pair, can be used to write the unlock sequence.

11.4.3 STARTING AND STOPPING A PROGRAMMING CYCLE

Once the unlock key sequence has been written to the NVMKEY register, the WR bit (NVMCON<15>) is used to start and stop an erase or write cycle. Setting the WR bit initiates the programming cycle. Clearing the WR bit terminates the programming cycle.

All erase and write cycles must be externally timed. An external delay must be used between setting and clearing the WR bit. Starting and stopping a programming cycle is performed as follows:

```
BSET    NVMCON, #WR
<Wait 2 ms>
BCLR    NVMCON, #WR
```

11.5 Erasing Program Memory in Normal-Voltage Systems

The procedure for erasing program memory (all code memory, data memory, executive memory and code-protect bits) consists of setting NVMCON to 0x407F, unlocking NVMCON for erasing and then executing the programming cycle. This method of bulk erasing program memory only works for systems where VDD is between 4.5 volts and 5.5 volts. The method for erasing program memory for systems with a lower VDD (3.0 volts–4.5 volts) is described in [Section 6.1 “Erasing Memory”](#).

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Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

Note: Program memory must be erased before writing any data to program memory.

TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS)

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Set NVMCON to program the FBS Configuration register.⁽¹⁾		
0000	24008A	MOV #0x4008, W10
0000	883B0A	MOV W10, NVMCON
Step 3: Initialize the TBLPAG and write pointer (W7) for TBLWT instruction for Configuration register.⁽¹⁾		
0000	200F80	MOV #0xF8, W0
0000	880190	MOV W0, TBLPAG
0000	200067	MOV #0x6, W7
Step 4: Load the Configuration Register data to W6.⁽¹⁾		
0000	EB0300	CLR W6
0000	000000	NOP
Step 5: Load the Configuration Register write latch. Advance W7 to point to next Configuration register.⁽¹⁾		
0000	BB1B86	TBLWTL W6, [W7++]
Step 6: Unlock the NVMCON for programming the Configuration register.⁽¹⁾		
0000	200558	MOV #0x55, W8
0000	200AA9	MOV #0xAA, W9
0000	883B38	MOV W8, NVMKEY
0000	883B39	MOV W9, NVMKEY
Step 7: Initiate the programming cycle.⁽¹⁾		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 2 ms
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 8: Repeat steps 5-7 one time to program 0x0000 to RESERVED2 Configuration register.⁽¹⁾		
Step 9: Set the NVMCON to erase all Program Memory.		
00000	2407FA	MOV #0x407F, W10
0000	883B0A	MOV W10, NVMCON
Step 10: Unlock the NVMCON for programming.		

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

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11.6 Erasing Program Memory in Low-Voltage Systems

The procedure for erasing program memory (all code memory and data memory) in low-voltage systems (with VDD between 2.5 volts and 4.5 volts) is quite different than the procedure for erasing program memory in normal-voltage systems. Instead of using a Bulk Erase operation, each region of memory must be individually erased by row. Namely, all of the code memory, executive memory and data memory must be erased one row at a time. This procedure is detailed in [Table 11-5](#).

Due to security restrictions, the FBS, FSS and FGS register cannot be erased in low-voltage systems. Once any bits in the FGS register are programmed to '0', they can only be set back to '1' by performing a Bulk Erase in a normal-voltage system. Alternatively, a Segment Erase operation can be performed instead of a Bulk Erase.

Normal-voltage systems can also be used to erase program memory as shown in [Table 11-5](#). However, since this method is more time-consuming and does not clear the code-protect bits, it is not recommended.

Note: Program memory must be erased before writing any data to program memory.

TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS)

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize NVMADR and NVMADRU to erase code memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	883B26	MOV W6, NVMADRU
0000	200407	MOV #0x40, W7
Step 3: Set NVMCON to erase 1 row of code memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
Step 4: Unlock the NVMCON to erase 1 row of code memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 5: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see Section 13.0 “AC/DC Characteristics and Timing Requirements”)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP

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11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed

during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Set the NVMCON to write 16 data words.		
0000	24005A	MOV #0x4005, W10
0000	883B0A	MOV W10, NVMCON
Step 3: Initialize the write pointer (W7) for TBLWT instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
Step 4: Load W0:W3 with the next 4 data words to program.		
0000	2xxxx0	MOV #<WORD0>, W0
0000	2xxxx1	MOV #<WORD1>, W1
0000	2xxxx2	MOV #<WORD2>, W2
0000	2xxxx3	MOV #<WORD3>, W3
Step 5: Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.		

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11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 4: Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
Step 5: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat steps 3-5 until all desired data memory is read.		

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12.2 Programming Verification

After the programming executive has been programmed to executive memory using ICSP, it must be verified. Verification is performed by reading out the contents of executive memory and comparing it with the image of the programming executive stored in the programmer.

Reading the contents of executive memory can be performed using the same technique described in [Section 11.10 “Reading Code Memory”](#). A procedure for reading executive memory is shown in [Table 12-2](#). Note that in Step 2, the TBLPAG register is set to 0x80 such that executive memory may be read.

TABLE 12-2: READING EXECUTIVE MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	EB0300	CLR W6
Step 3: Initialize the write pointer (W7), and store the next four locations of executive memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP

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TABLE 13-1: AC/DC CHARACTERISTICS (CONTINUED)

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	Sym	Characteristic	Min	Max	Units	Conditions
P9b	TDLY5	Delay between PGD ↓ by programming executive to PGD released by programming executive	15	—	μs	—
P10	TDLY6	Delay between PGD released by programming executive to first PGC ↑ of response	5	—	μs	—
P11	TDLY7	Delay between clocking out response words	10	—	μs	—
P12a	TPROG	Row Programming cycle time	1	4	ms	ICSP mode
P12b	TPROG	Row Programming cycle time	0.8	2.6	ms	Enhanced ICSP mode
P13a	TERA	Bulk/Row Erase cycle time	1	4	ms	ICSP mode
P13b	TERA	Bulk/Row Erase cycle time	0.8	2.6	ms	Enhanced ICSP mode